

**Amendments to the Specification:**

**Replace the paragraph on pg. 2, beginning at line 30 of the specification as originally filed with the following replacement paragraph:**

--The document U.S. Pat. No. 3,739,217 discloses that the coupling-out of light from gallium ~~phosphite~~ phosphide crystals can be improved by roughening the surface.--

**Replace the paragraph on pg. 2, beginning at line 30, bridging pg. 3 of the specification as originally filed with the following replacement paragraph:**

--This known method for roughening the surface of a body has the disadvantage that it is not suitable for application in the case of semiconductor bodies made of the material aluminum gallium indium ~~phosphite~~ phosphide or aluminum gallium indium nitride. The reason for this is that the dry etching methods used have an excessively low selectivity with regard to the polystyrene balls. This means that the semiconductor body is etched only very slowly in comparison with the balls, for which reason the balls serving as an etching mask will already have disappeared at a very early point in time in the etching process when only a very small structure depth has been etched into the surface of the body. The consequence of this is that the required ratio of etching depth to structure width of 0.25 to 5 cannot be achieved. This ratio is required in order to efficiently improve the coupling-out of light from the semiconductor body.--

**Replace the paragraph on pg. 5, beginning at line 4 of the specification as originally filed with the following replacement paragraph:**

--In one embodiment of the method, the body contains aluminum gallium indium ~~phosphite~~ phosphide (AlGaInP). This semiconductor material is advantageously used for light emitting diodes which emit in the red or blue spectral range. This semiconductor material is optionally deposited on silicon carbide or on a gallium arsenide substrate.--

**Replace the paragraph on pg. 8, beginning at line 23 of the specification as originally filed with the following replacement paragraph:**

--Furthermore, an optoelectronic component having a semiconductor body is also specified. Said semiconductor body contains aluminum gallium indium ~~phosphite~~ phosphide or aluminum gallium indium nitride. Furthermore, the surface of the body is patterned, the following holding true for the width of the structures in comparison with the depth of the structures or the etching depth:  $0.25 < t/b < 5$ . Furthermore, the same component is specified but the semiconductor body contains aluminum gallium indium nitride instead of aluminum gallium indium ~~phosphite~~ phosphide. Such optoelectronic components, for example LEDs, can be produced for the first time with the aid of the method presented here. The methods disclosed in the prior art are not suitable for producing the ratio of t to b described here.--